The RF Line NPN Silicon RF Power Transistors

... designed for 13.6 volt VHF large-signal class C and class AB linear power amplifier applications in commercial and industrial equipment.

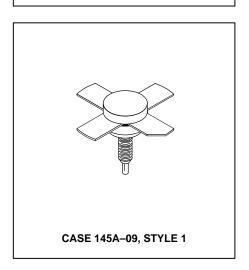
- High Common Emitter Power Gain
- Specified 13.6 V, 160 MHz Performance: Output Power = 40 Watts Power Gain = 9.0 dB Min Efficiency = 55% Min
- · Load Mismatch Capability at Rated Voltage and RF Drive
- · Silicon Nitride Passivated
- Low Intermodulation Distortion, $d_3 = -30 \text{ dB Typ}$

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO	16	Vdc
Collector-Base Voltage	V _{CBO}	36	Vdc
Emitter-Base Voltage	V _{EBO}	4.0	Vdc
Collector Current — Continuous	lc	8.0	Adc
Total Device Dissipation @ T _C = 25°C (1) Derate above 25°C	PD	100 0.57	Watts W/°C
Storage Temperature Range	T _{stg}	-65 to +150	°C

MRF240

40 W, 145-175 MHz RF POWER TRANSISTORS NPN SILICON



THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case (2)	$R_{\theta JC}$	1.75	°C/W

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (I _C = 20 mAdc, I _B = 0)	V(BR)CEO	16	_	_	Vdc
Collector–Emitter Breakdown Voltage (I _C = 20 mAdc, V _{BE} = 0)	V(BR)CES	36	_	_	Vdc
Emitter–Base Breakdown Voltage $(I_E = 5.0 \text{ mAdc}, I_C = 0)$	V(BR)EBO	4.0	_	_	Vdc
Collector Cutoff Current (V _{CB} = 15 Vdc, I _E = 0)	I _{CBO}	_	_	10	mAdc
ON CHARACTERISTICS					
DC Current Gain (IC = 4.0 Adc, V_{CE} = 5.0 Vdc)	hFE	10	70	150	_
DYNAMIC CHARACTERISTICS					
Output Capacitance (V _{CB} = 12.5 Vdc, I _E = 0, f = 1.0 MHz)	C _{ob}	_	90	125	pF

NOTES: (continued)

- 1. This device is designed for RF operation. The total device dissipation rating applies only when the device is operated as an RF amplifier.
- 2. Thermal Resistance is determined under specified RF operating conditions by infrared measurement techniques.

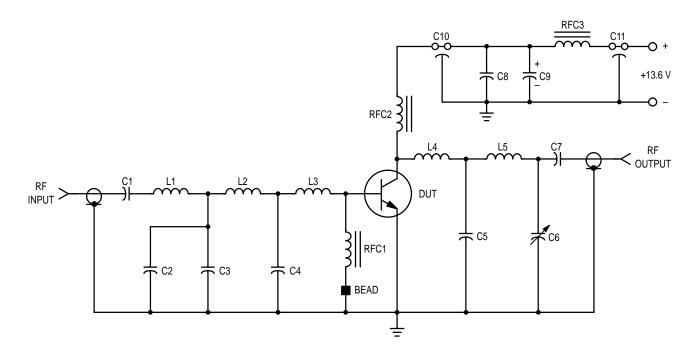


ELECTRICAL CHARACTERISTICS — **continued** (T_C = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
FUNCTIONAL TESTS					
Common–Emitter Amplifier Power Gain (V _{CC} = 13.6 Vdc, P _{out} = 40 W, f = 160 MHz)	GPE	9.0	10	_	dB
Collector Efficiency (V _{CC} = 13.6 Vdc, P _{out} = 40 W, f = 160 MHz)	η	55	_	_	%
TYPICAL SSB PERFORMANCE					
Intermodulation Distortion (3) (V _{CC} = 13.6 Vdc, P_{Out} = 35 W (PEP), f1 = 146 MHz, f2 = 146.002 MHz, I_{CQ} = 50 mAdc)	IMD (d ₃)	I	-30		dB

NOTE:

3. To MIL-STD-1311 Version A, Test Method 2204B, Two Tone, Reference Each Tone.



C1 — 200 pF, 350 Vdc, UNELCO

C2 — 100 pF, 350 Vdc, UNELCO

C3 — 40 pF, 350 Vdc, UNELCO

C4, C5 — 80 pF, 350 Vdc, UNELCO

C6 — 1.0-20 pF, ARCO Trimmer

C7 — 100 pF 350 Vdc, UNELCO

 $C8 - 0.1 \,\mu\text{F}$ ERIE Disc Ceramic

 $C9 - 1.0 \, \mu F \, TANTALUM$

C10, C11 — 680 pF ALLEN BRADLEY Feedthru

RFC1 — $0.15 \,\mu H$ Molded Choke

RFC2 — 10 Turns, #18 AWG on 470 Ohm,

1.0 Watt Resistor

Bead — FERROXCUBE Bead

RFC3 — FERROXCUBE Choke, VK200-4B

L1 — 3.3 x 0.2 cm AIRLINE Inductor

L2 - 1.0 x 0.2 cm AIRLINE Inductor

L3 — 1.2 x 0.6 cm Brass Pad

 $L4 - 1.2 \times 0.6$ cm Brass Pad and

2.0 x 0.2 cm AIRLINE Inductor

Board — G10, ϵ_{Γ} = 5, t = 62 mils

2 sided, 2 oz. Clad

Connectors: Type N

Figure 1. 160 MHz Test Circuit Schematic

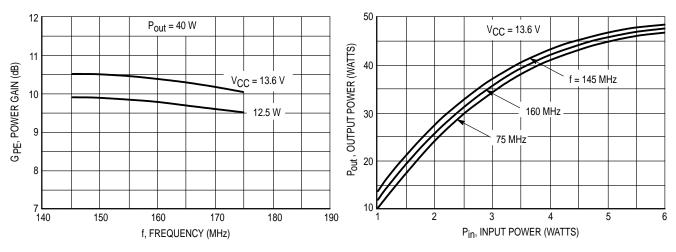


Figure 2. Power Gain versus Frequency

Figure 3. Output Power versus Input Power

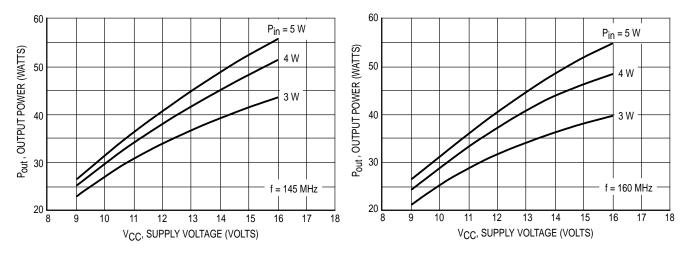


Figure 4. Output Power versus Supply Voltage

Figure 5. Output Power versus Supply Voltage

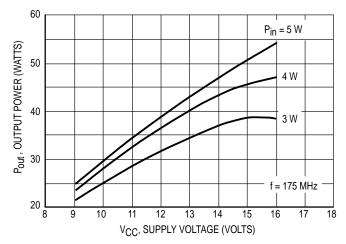


Figure 6. Output Power versus Supply Voltage

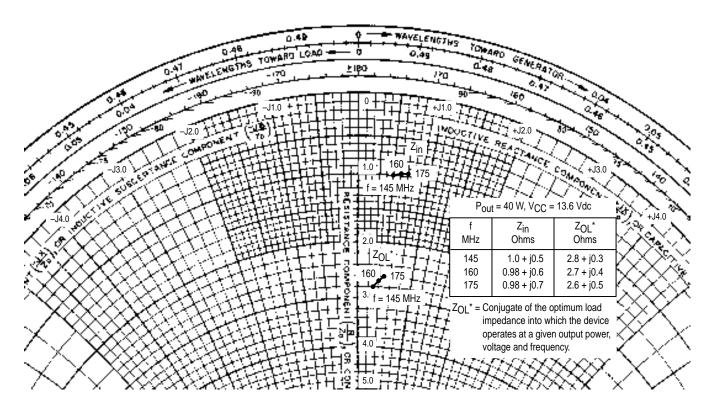
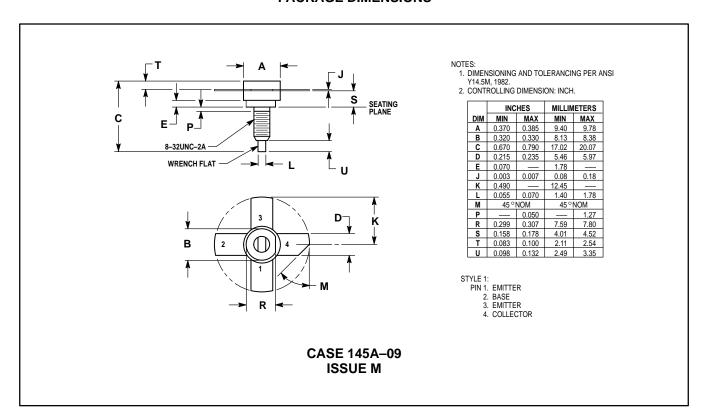


Figure 7. Series Equivalent Input/Output Impedances

PACKAGE DIMENSIONS



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